# MSKSEMI 美森科













**ESD** 

TVS

TSS

MOV

GDT

PLED

# MMBT3904DFN

**Product specification** 





#### **Features**

- Low profile package
- Ideal for automated placement
- Low saturation voltages
- High voltage capability
- High Stability and High Reliability
- RoHS Compliant

## **Applications**

- amplifying signal
- Electronic switch
- Oscillating circuit
- Variable resistance
- Lighting applications

## **Appearance & Symbol**

PACKAGE OUTLINE	Pin Configuration	Marking
1: Base 2: Emitter 3: Collector	Base	6P



#### Absolute Maximum Ratings (T=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	Vсво	60	V
Collector-Emitter Voltage	Vceo	40	V
Emitter-Base Voltage	VEBO	6	V
Collector Current Continuous	Ic	0.2	А
Power Dissipation	P <sub>D</sub>	0.3	W
Operating Junction temperature	TJ	-55 to +150	$^{\circ}$
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	℃

## Electrical Characteristics (T=25℃ unless otherwise noted)

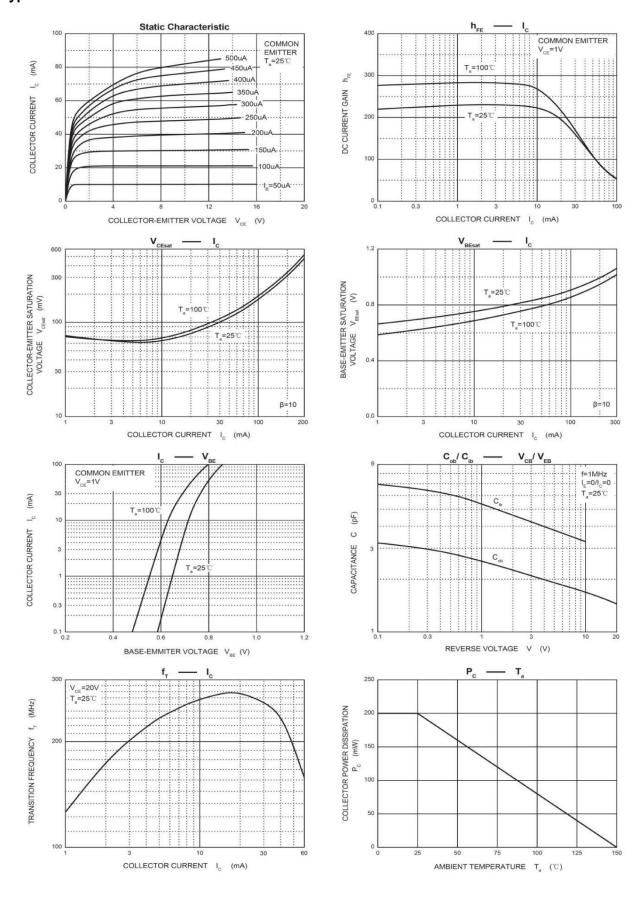
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	V <sub>CBO</sub>	I <sub>C</sub> =10μΑ, I <sub>E</sub> =0	60			V
Collector-Emitter Breakdown Voltage	V <sub>CER</sub>	I <sub>C</sub> =1mA,I <sub>B</sub> =0	40			V
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>E</sub> =10uA,I <sub>C</sub> =0	6			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0			100	nA
Collector Cut-Off Current	I <sub>CEX</sub>	V <sub>CE</sub> =30V,V <sub>EB(off)</sub> =3V			50	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V,I <sub>C</sub> =0			100	nA
	h <sub>FE</sub>	V <sub>CE</sub> =1V,I <sub>C</sub> =0.1mA	40			
		V <sub>CE</sub> =1V,I <sub>C</sub> =1mA	70			
DC current gain		V <sub>CE</sub> =1V,I <sub>C</sub> =10mA	100		300	
		V <sub>CE</sub> =1V,I <sub>C</sub> =50mA	60			
		V <sub>CE</sub> =1V,I <sub>C</sub> =100mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.3	V
Base -emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.95	V
Transition frequency	f⊤	V <sub>CE</sub> = 20V, I <sub>C</sub> =10mA,f=100MHz	300			MHZ
Delay Time	td	$V_{CC} = 3V, I_{C} = 10mA,$		35		
Rise time	tr	V <sub>BE(off)</sub> =-0.5V, I <sub>B1</sub> =1mA		35		ns
Storage time	ts	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA,		200		us
Fall time	tf	$I_{B1} = I_{B2} = 1 \text{mA}$		50		ns

## Classification of hee

Range 100-	300
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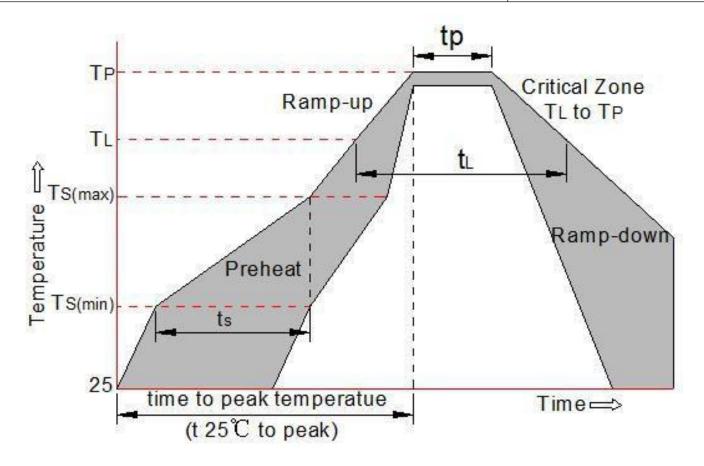
#### **Typical Characteristics**





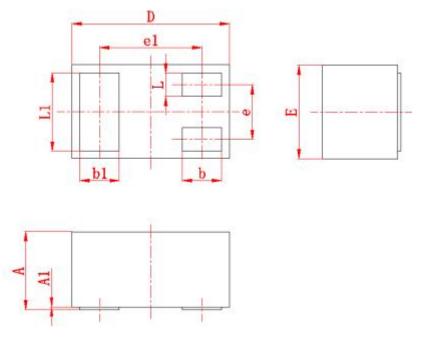
#### Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)	
	-Temperature Min (T <sub>s(min)</sub> )	+150℃	
Pre Heat	-Temperature Max(T <sub>s(max)</sub> )	+200℃	
riorioat	-Time (Min to Max) (ts)	60-180 secs.	
Average	Average ramp up rate (Liquid us Temp (T∟) to peak)		
	T <sub>s(max)</sub> to T <sub>L</sub> - Ramp-up Rate		
	-Temperature(T <sub>∟</sub> ) (Liquid us)	+217℃	
Reflow	-Temperature(t∟)	60-150 secs.	
Peak Temp (T <sub>p</sub> )		+260(+0/-5)°C	
Time within 5°C of actual Peak Temp (t₂)		30 secs. Max	
Ramp-down Rate		6℃/sec. Max	
Time 25℃ to Peak Temp (T <sub>P</sub> )		8 min. Max	
Do not exceed		not exceed +260℃	



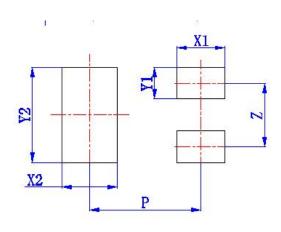


## Package mechanical data



Symbol	Millimeters		
	min	max	
А	0.4	0.5	
A1	0	0.05	
D	0.9	1.1	
E	0.55	0.65	
е	(0.35)		
e1	(0.65)		
b	0.2	0.3	
b1	0.2	0.3	
L	0.1	0.2	
L1	0.45 0.55		

## **Suggested Land Pattern**



Symbol	Dimension in Millimeters	
	typ	
X1	(0.3)	
X2	(0.35)	
Y1	(0.2)	
Y2	(0.6)	
Z	(0.4)	
Р	(0.7)	

## **REEL SPECIFICATION**

P/N	PKG	QTY
MMBT3904DFN	DFN1006-3	10000



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